

Flicker Noise Extraction for Scalable MOS Simulation Models

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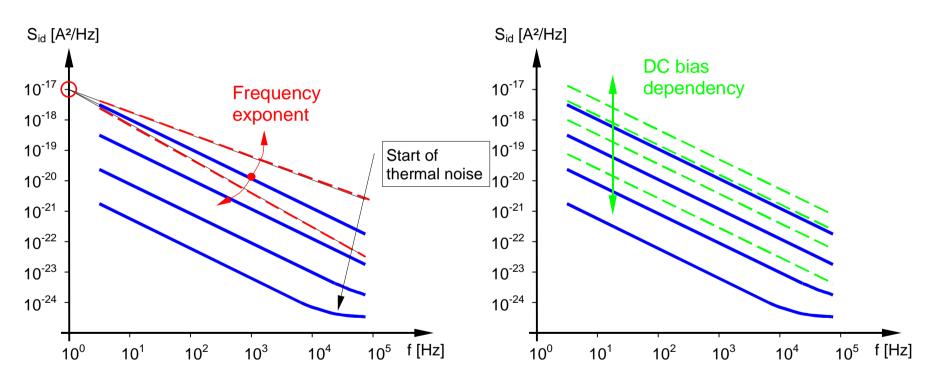
Content

- Flicker noise equations in modern MOS models
- Noise simulation in different simulators
- Steps in parameter extraction using a PSP example
- Problems to be solved
- Summary



Common Flicker Noise Models

The most MOS simulation models provide the following 2 principal degrees of freedom to adjust the flicker noise behavior.



+ Dimension dependency



BSIM3 Flicker Noise

$$NOIMOD=1,4,5$$

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$$S_{id}(f) = \frac{(KF) I_{DS}}{C_{OX} \cdot L_{eff}^{2} \cdot f^{EF}}$$
 "classic" SPICE model

NOIMOD=2,3,6

BSIM3 model

$$V_{gs} > V_{th} + 0.1$$
:

$$S_{id}(f) = \frac{k_B \cdot T \cdot q^2 \cdot \mu_{eff} \cdot I_{DS}}{C_{oxe} \left(L_{eff} - 2 * LINTNOI\right)^2 \cdot A_{bulk} \cdot f^{EF} \cdot 10^8}$$

$$\left(NOIA \cdot \log \left(\frac{N_o + 2 \cdot 10^{14}}{N_l + 2 \cdot 10^{14}}\right) + NOIB \left(N_o - N_l\right) + \frac{NOIC}{2} \cdot \left(N_o^2 - N_l^2\right)\right)$$

$$+\frac{k_{B} \cdot T \cdot I_{DS}^{2} \cdot \Delta L_{CLM}}{W_{eff} \left(L_{eff}-2*LINTNOI\right)^{2} \cdot f^{EF} \cdot 10^{8}} \cdot \frac{NOIA+NOIB \cdot N_{l}+NOIC \cdot N_{l}^{2}}{\left(N_{l}+N^{*}\right)}$$

$$V_{as} < V_{th} + 0.1$$

$$V_{gs} < V_{th} + 0.1: S_{id}(f) = \frac{S_{li'mit} \cdot S_{wi}}{S_{li'mit} + S_{wi}}, S_{wi}(f) = \frac{NOIA \cdot V_{tm} \cdot I_{DS}^{2}}{W_{eff} \cdot L_{eff} \cdot f^{EF} \cdot 4 \cdot 10^{36}}$$



BSIM4 Flicker Noise

FNOIMOD=0

$$S_{id} = \frac{KF}{C_{OX} \cdot L_{eff}^{2} \cdot f^{EF}}$$
 "classic" SPICE model

FNOIMOD=1

Inversion:

$$S_{id,inv}(f) = \frac{k_{B} \cdot T \cdot q^{2} \cdot \mu_{eff} \cdot I_{DS}}{C_{oxe} (L_{eff} - 2 * LINTNOI)^{2} \cdot A_{bulk} \cdot f^{(EF)} \cdot 10^{10}} \cdot \left(\frac{N_{O} + N^{*}}{N_{l} + N^{*}} \right) + \frac{NOIB}{N_{O}} \cdot (N_{O} - N_{l}) + \frac{NOIC}{2} \cdot (N_{O}^{2} - N_{l}^{2}) \right) + \frac{k_{B} \cdot T \cdot I_{DS}^{2} \cdot \Delta L_{CLM}}{W_{off} (L_{eff} - 2 * LINTNOI)^{2} \cdot f^{(EF)} \cdot 10^{10}} \cdot \frac{NOIA + NOIB \cdot N_{l} + NOIC \cdot N_{l}^{2}}{(N_{l} + N^{*})^{2}}$$

SubVth:

$$S_{id}(f) = \frac{S_{id,inv}(f) \cdot S_{id,subVt}(f)}{S_{id,inv}(f) + S_{id,subVt}(f)}, \quad S_{id,subVt}(f) = \frac{NOIA \cdot k_B \cdot T \cdot I_{DS}^{2}}{W_{eff} \cdot L_{eff} \cdot f^{EF} \cdot N^{*2} \cdot 10^{10}}$$



PSP Flicker Noise

Local model:

$$S_{fl}(f) = \frac{\mathbf{q} \cdot \mathbf{\Phi}_{T}^{2} \cdot \beta \cdot I_{DS}}{f \cdot \mathbf{Q}_{ox} \cdot G_{vsat} \cdot N^{*}} \cdot \left[(NFA + NFB)N^{*} + (NFC)N^{*2} \right) \cdot \ln \left(\frac{N_{m}^{*} + \Delta N/2}{N_{m}^{*} - \Delta N/2} \right) \right] + \left(NFB + NFC \cdot \left[N_{m}^{*} - 2 \cdot N^{*} \right] \cdot \Delta N \right)$$

Scaling equation:

$$NFA = NFALW \cdot \frac{W_{EN} \cdot L_{EN}}{W_E \cdot L_E}$$

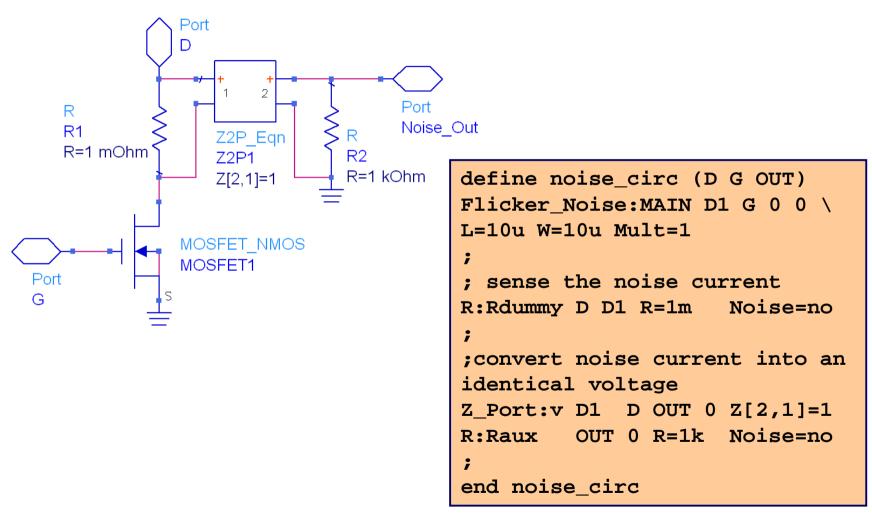
$$NFB = NFBLW \cdot \frac{W_{EN} \cdot L_{EN}}{W_E \cdot L_E}$$

$$NVC = NFCLW \cdot \frac{W_{EN} \cdot L_{EN}}{W_E \cdot L_E}$$

Fixed frequency exponent of 1!

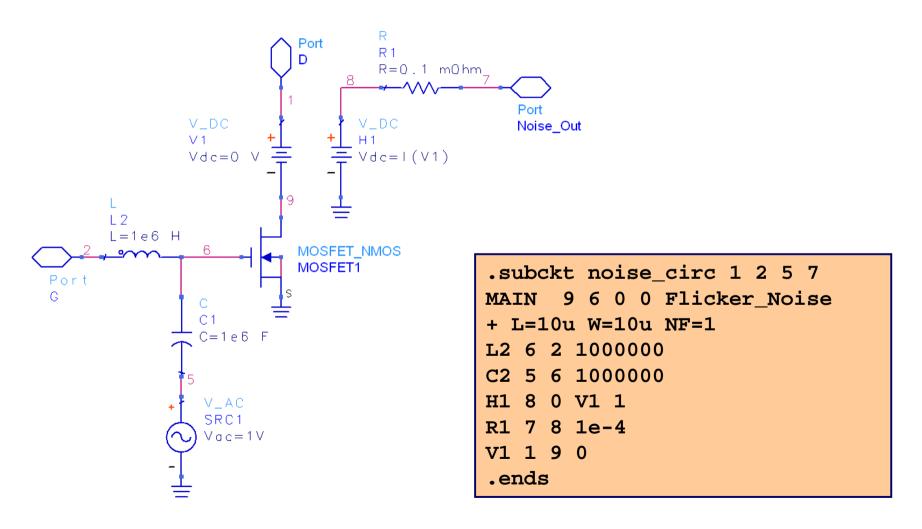


Noise in ADS





Noise in Spice, HSPICE





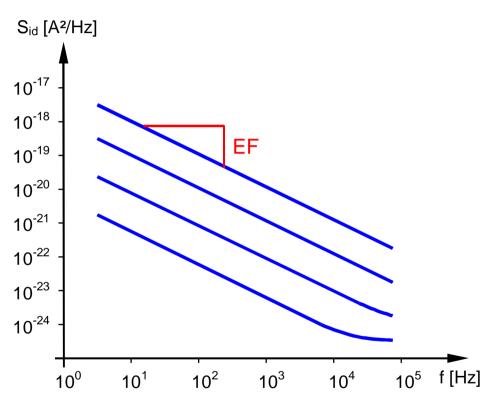
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- Flicker noise equations in modern MOS models
- Noise simulation in different simulators
- Steps in parameter extraction using a PSP example
 - Measurement (see paper from IHP, Falk Korndörfer)
 - Determination of the frequency exponent
 Determination of bias dependency

 - Extraction of parameters for scalable noise models shown with an example using the PSP model
- Problems to be solved
- Summary
- *) Based on the work of Knoblinger, Grabinski, Sischka



Frequency Exponent (1)



If the model provides a frequency exponent, it can be derived from the slope of the measured curves in logarithmic representation:

(Example for SPICE model, the other models behave similar)

$$S_{id}(f) = \frac{KF \cdot I_{DS}^{AF}}{C_{OX} \cdot L_{eff}^{2} \cdot f^{EF}}$$

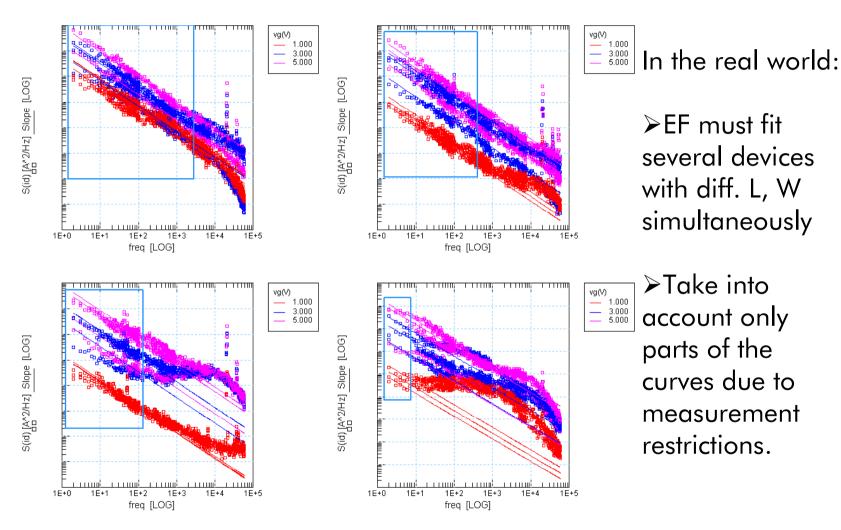
$$S_{id}(f) = con \cdot f^{-EF}$$

$$\log(S_{id}(f)) = \log(con) - EF \cdot \log(f)$$

$$y = c + m \cdot x$$



Frequency Exponent (2)

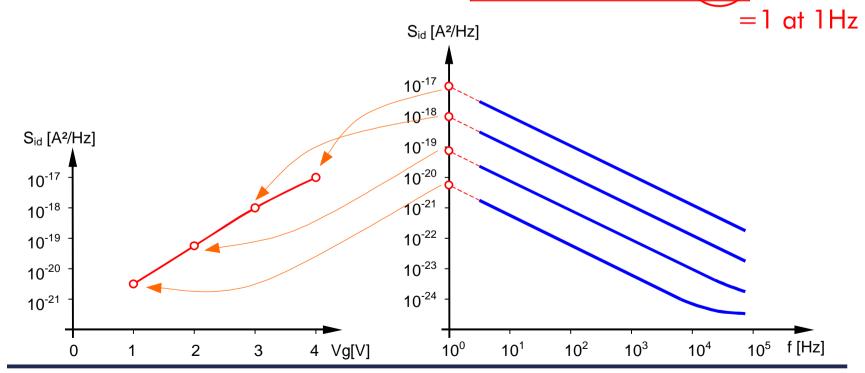




Once the slope is given, the noise values at 1Hz can be determined by extrapolating the measured curve to 1Hz.

(Example for SPICE model, the other models behave similar)

$$S_{id}(f) = \frac{KF \cdot I_{DS}^{AF}}{C_{OX} \cdot L_{eff}^{2} \cdot f^{EF}}$$





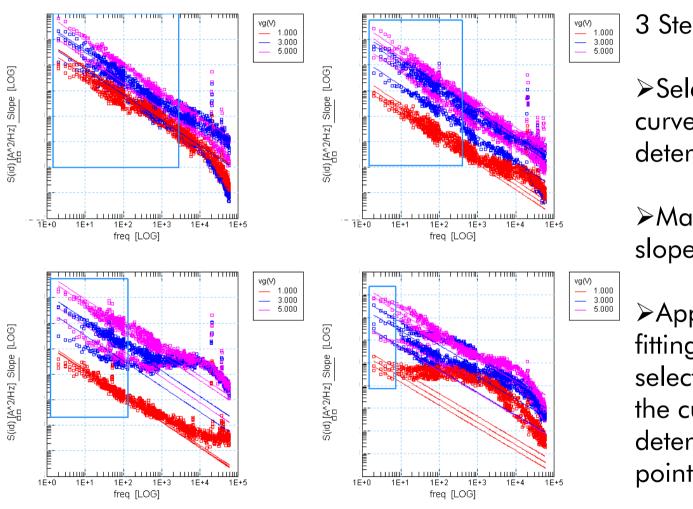
3 Steps:

Select range of curves to determine slope

Make curves slopeless

Apply linear fitting to the selected range of the curve and determine crosspoint at 1Hz

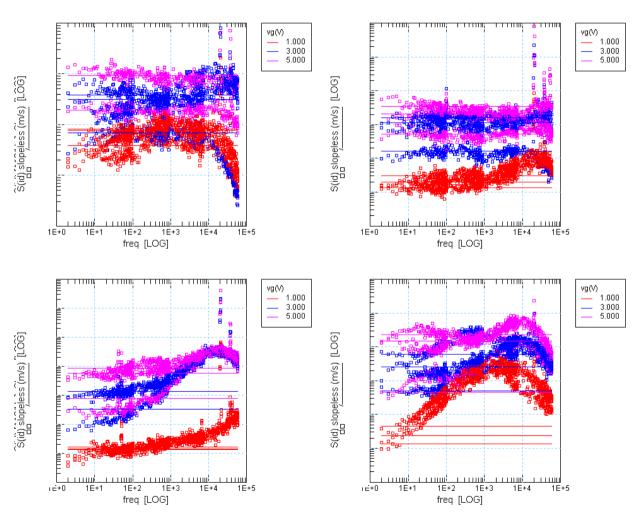




3 Steps:

- ➤ Select range of curves to determine slope
- ➤ Make curves slopeless
- ➤ Apply linear fitting to the selected range of the curve and determine crosspoint at 1Hz

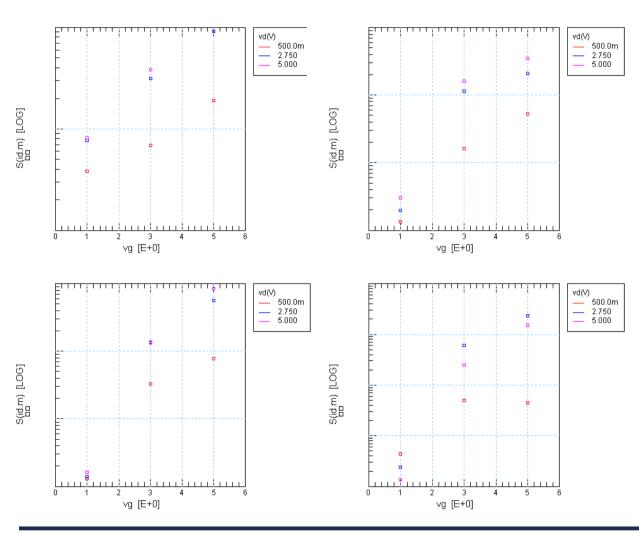




3 Steps:

- Select range of curves to determine slope
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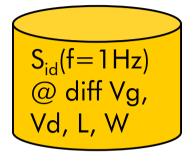


3 Steps:

- Select range of curves to determine slope
- ➤ Make curves slopeless
- Apply linear fitting to the selected range of the curve and determine crosspoint at 1Hz



Parameter Extraction - PSP (1)







S_{fl}(1Hz)=f(Parameter, Dimensions, DC Bias)

Solver

PSP: PSP1020 Par. L, W, MULT VG, VD

Iterative Solution
using a modified
LevenbergMarquardt algorithm



Noise parameters

PSP: NFALW, NFBLW, NFCLW



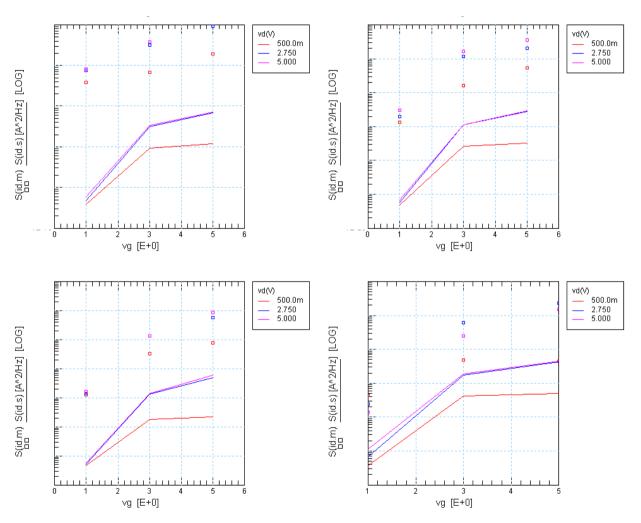
Parameter Extraction - PSP (2)

Example parameter extraction process:

- Simulation with default values of NFALW, NFBLW, NFCLW
- Perform
 extraction in
 ca. 1s and
 repeat
 simulation



Parameter Extraction - PSP (2)

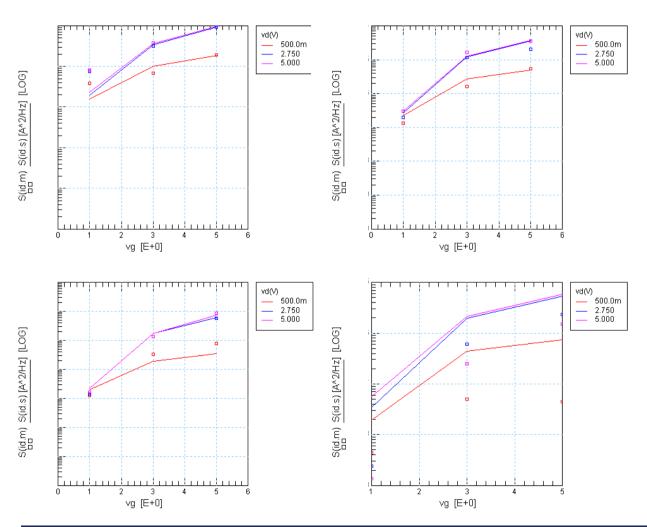


Example parameter extraction process:

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Parameter Extraction - PSP (2)

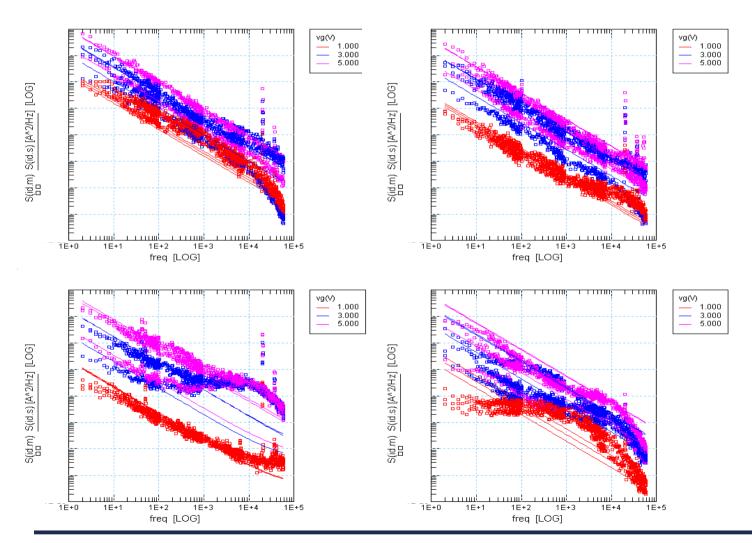


Example parameter extraction process:

- Simulation with default values of NFALW, NFBLW, NFCLW
- Perform
 extraction in
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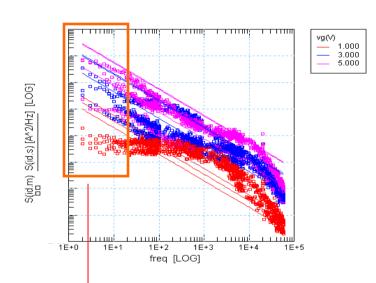
MOS Parameter Extraction – PSP (3)



Final result for 4 different transistor dimensions.



Problems to be solved



Fitting for small device cannot be improved in this area without the distortion of the other devices.

The scalability of the simulation models is still not good enough.

The PSP scaling equation:

$$NFA = NFALW \cdot \frac{W_{EN} \cdot L_{EN}}{W_E \cdot L_E}$$

$$NFB = NFBLW \cdot \frac{W_{EN} \cdot L_{EN}}{W_E \cdot L_E}$$

$$NVC = NFCLW \cdot \frac{W_{EN} \cdot L_{EN}}{W_E \cdot L_E}$$

does not allow to modify parameters independently for L and W. Actually, only the product L·W is taken into account.



Summary

- Together with the measurement of flicker noise (presented by Falk Korndörfer, IHP), the shown extraction strategy is the basis of a complete noise modeling method.
- The very effective simultaneous extraction of flicker noise parameters for different devices with different dimensions is the key improvement of this tool.
- The shown methodology for PSP was implemented for common MOS models (BSIM3, BSIM4) and can be easily extended to other models like HiSIM2 etc.
- The co-operation between IHP and AdMOS resulted in a commercial available Flicker Noise Modeling Tool. For details, please see:

<u>www.admos.de</u> → Products → Flicker Noise System